TPW PTO/SB/21 (09-04)

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		10/81	15,312		
TRANSMITTALL PE	Filing Date	April	April 1, 2004		
FORM/	First Named Inventor	Yung	-Tin Chen		
JUN 2 8 200		1756	S		
(to be used for all correspondent after initial filing)	Examiner Name	Stepl	nen D Rosasco		
Total Number of Pages in This Submission ADEN	Attorney Docket Number	MA-1	17		
Total Number of Pages in This Submission April					
E	NCLOSURES (Check all	that apply			
Fee Transmittal Form Fee Attached Amendment/Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Reply to Missing Parts/ Incomplete Application Reply to Missing Parts under 37 CFR 1.52 or 1.53	Drawing(s) Licensing-related Papers Petition Petition to Convert to a Provisional Application Power of Attorney, Revocatio Change of Correspondence A Terminal Disclaimer Request for Refund CD, Number of CD(s) Landscape Table on CD temarks	ddress	Appeal of Appeal (Appeal (Appeal Status Other I below)	Enclosure(s) (please Identify : n receipt postcard	
SIGNATUE	RE OF APPLICANT, ATTO	PNEY O	R AGENT		
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Matrix Semiconductor, Inc	//				
Signature	6				
Printed name Pamela J. Squyres			•	·	
Date	Γ	Reg. No.	52246		
Date 6/23/05	<u> </u>	<u> </u>	32240		
CERT	IFICATE OF TRANSMISS	ION/MAI	LING		
I hereby certify that this correspondence is being sufficient postage as first class mail in an envelop the date shown below:	facsimile transmitted to the USPT be addressed to: Commissioner fo	O or depos Patents, P	ited with the Uni P.O. Box 1450, A	ited States Postal Service with Alexandria, VA 22313-1450 on	
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Typed or printed name LORIE	ARKLEY ARKLEY		Date	6/24/05	

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and1.14. This collection is estimated to 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Yung-Tin Chen

Application No.:

10/815,312

10/615,512

Filed: April 1, 2004

Title: Photomask Features with Chromeless Nonprinting Phase Shifting

Window

Attorney Docket No.: MA-117

Group Art Unit: 1756

Examiner: Stephen D. Rosasco

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir or Madam,

Pursuant to the obligation under 37 CFR § 1.56 and in conformance with 37 CFR §§ 1.97-1.99, Applicant hereby submits documents A1-A37 as listed on the attached form PTO-1449 for consideration by the Examiner. Copies of reference documents A9-A37 are enclosed herewith. Applicant requests that the Examiner review the entire disclosure of these documents and make them of record.

The filing of this Information Disclosure Statement does not constitute an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR §1.56(b). Further Applicant reserves the right to contest that any of the information submitted herewith is prior art against the present application.

Dated:

Respectfully submitted,

Pamela J. Squyres

Agent for Applicants Reg. No. 52,246

Pamela J. Squyres Matrix Semiconductor 3230 Scott Blvd Santa Clara, CA 95054 Tel. 408-869-2921

Substitute for form 1449A/PTO	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/815,312
(Use as many sheets as necessary)	Filing Date	April 1, 2004
OIPE	First Named Inventor	Chen, Yung-Tin
(6)	Group Art Unit	1756
JUN 2 8 2005 (5)	Examiner Name	Rosasco, Stephen
Sheet 1 of 3	Attorney Docket No: N	MA-117

	US PATENT DOCUMENTS						
Examiner Initial *	Cite No	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	A1	5,240796	08/31/1993	Lee et al.			
	A2	6,057063	05/02/2000	Liebmann et al.			- <u>-</u>
	A3	6,482555	11/19/2002	Chen et al.			
	A4	6,523165	02/18/2003	Liu et al.			
	A5	6,541165	04/01/2003	Pierrat			
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	A7	6,569583	05/27/2003	Cho et al.			
_	A8	20030022074	01/30/2003	Nolscher			

	FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

	ОТНІ	ER DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	include name of the author (In CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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DATE CONSIDERED

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ser the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid DMB control number. Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE 10/815,312 **Application Number** STATEMENT BY APPLICANT **Filing Date** April 1, 2004 Chen, Yung-Tin **First Named Inventor** 1756 **Group Art Unit Examiner Name** Rosasco, Stephen Attorney Docket No: MA-117 Sheet 2 of 3

	OTH	ER DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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Substitute for form 1449A/PTO	Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/815,312	
	Filing Date	April 1, 2004	
	First Named Inventor	Chen, Yung-Tin	
,	Group Art Unit	1756	
	Examiner Name	Rosasco, Stephen	
Sheet 3 of 3	MA-117		

	OTH	ER DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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